

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

SFT1350 — General-Purpose Switching Device **Applications**

Features

- ON-resistance RDS(on)1= $45m\Omega(typ.)$ Input Capacitance Ciss=590pF(typ.)
- 4.5V drive

- · Halogen free compliance
- · Protection diode in

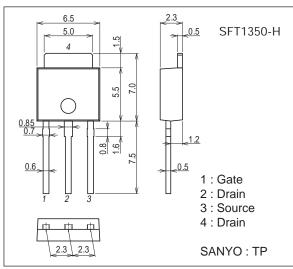
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-40	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		-19	Α
Drain Current (PW≤10μs)	IDP	PW≤10μs, duty cycle≤1%	-76	Α
Allowable Power Dissipation	Do		1.0	W
Allowable Power Dissipation	PD	Tc=25°C	23	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

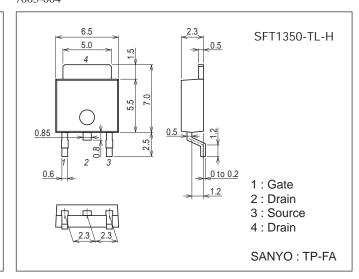
Package Dimensions unit : mm (typ)

7518-004



Package Dimensions unit: mm (typ)

7003-004



Product & Package Information

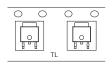
- Package : TP
- JEITA, JEDEC: SC-64, TO-251
- Minimum Packing Quantity: 500 pcs./bag

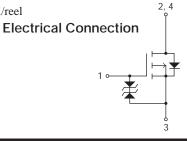
Marking (TP, TP-FA)



- Package: TP-FA
- JEITA, JEDEC: SC-63, TO-252
- Minimum Packing Quantity: 700 pcs./reel

Packing Type (TP-FA): TL





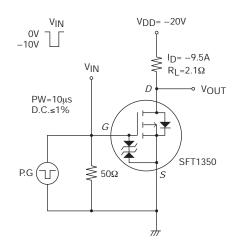
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http://semicon.sanyo.com/en/network

Electrical Characteristics at Ta=25°C

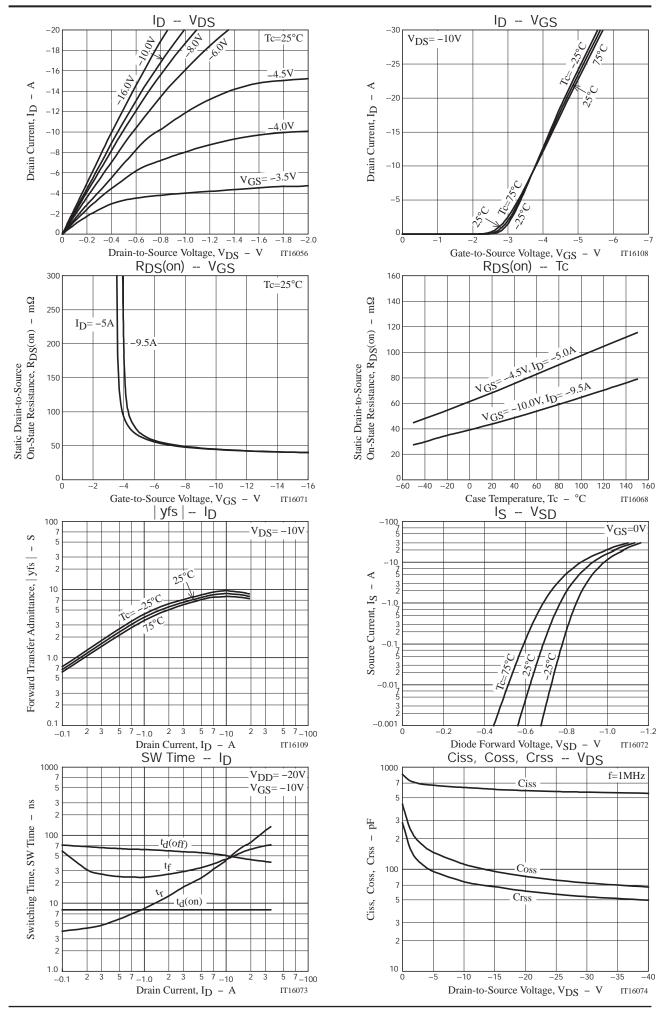
Parameter	Symbol	Conditions		Ratings	Unit	
Parameter	Symbol	Conditions	min	typ	max	Offit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-40			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-40V, V _{GS} =0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =-10V, I _D =-1mA	-1.7		-2.6	V
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-9.5A		8.7		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-9.5A, V _G S=-10V		45	59	mΩ
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =-5A, V _G S=-4.5V		73	105	mΩ
Input Capacitance	Ciss			590		pF
Output Capacitance	Capacitance Coss VD e Transfer Capacitance Crss			85		рF
Reverse Transfer Capacitance	Crss			61		pF
Turn-ON Delay Time	t _d (on)			8		ns
Rise Time	t _r	Sac appolition Test Circuit		40		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		52		ns
Fall Time	tf			44		ns
Total Gate Charge	Qg			12		nC
Rise Time t_{Γ} Turn-OFF Delay Time $t_{d}(\text{off})$ Fall Time t_{f} Total Gate Charge Qg Gate-to-Source Charge Qgs		V _{DS} =-20V, V _{GS} =-10V, I _D =-19A		3.6		nC
Gate-to-Drain "Miller" Charge	Qgd			2.0		nC
Diode Forward Voltage	VSD	IS=-19A, VGS=0V		-1.03	-1.2	V

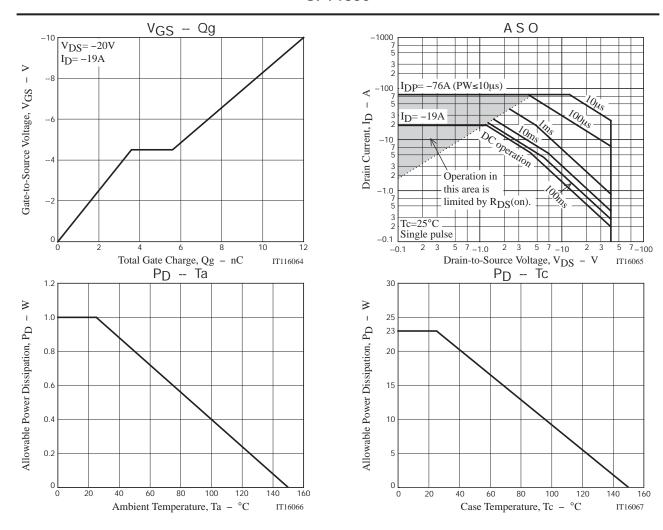
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
SFT1350-H	TP	500pcs./bag	Db Free and Helegen Free
SFT1350-TL-H	TP-FA	700pcs./reel	Pb Free and Halogen Free



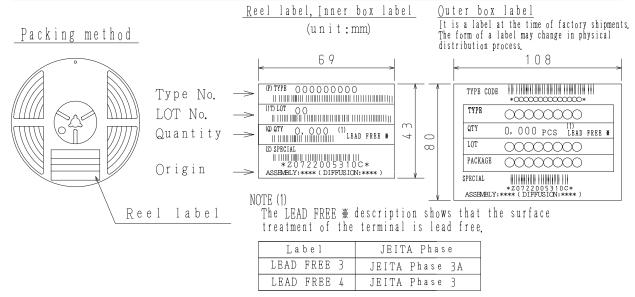


Taping Specification

SFT1350-TL-H

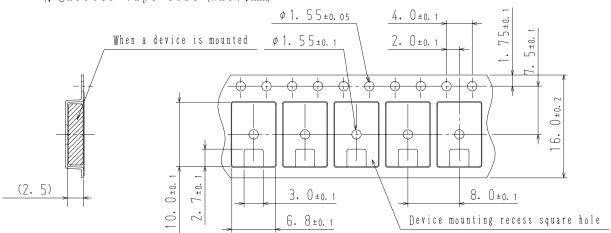
Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
TP-FA	TP	700	2, 100	12, 600	3 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	

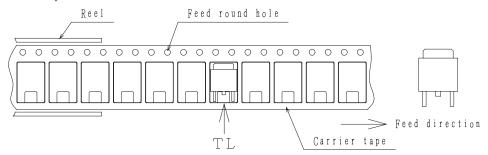


Taping configuration

1. Carrier tape size (unit:mm)



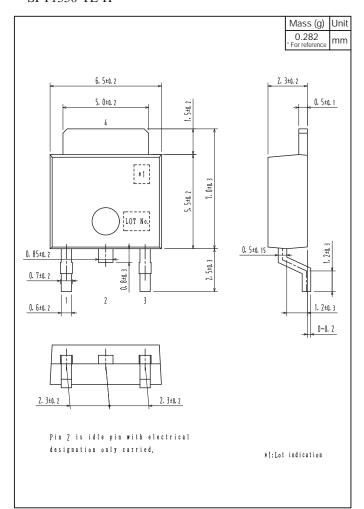
7. Device placement direction

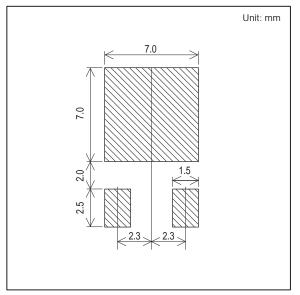


Those with one electrode terminal on the feed hole side·····TL

Outline Drawing SFT1350-TL-H

Land Pattern Example





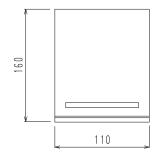
Bag Packing Specification

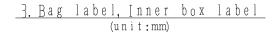
SFT1350-H

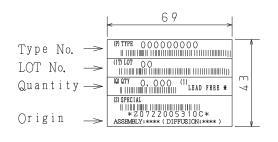
1. Packing Format

Package Name		Maximum Numbe	r of devices cont	ained (pcs)		
I donago mamo	Вад	Inner box	Outer box			
TP		B-1	A-1	A-2		
1 1 1	500	10,000	50,000	30,000		
		Packing format (Dimensions:mm (external))				
		Inner box	Outer	box		
		B-1	A-1	A-2		
		445×225×55	470×250×300	470×250×190		

2. Bag dimensions (unit:mm)





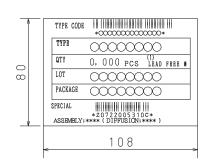


4. Outer box label (unit:mm)

It is a label at the time of factory shipments, The form of a label may change in physical distribution process,

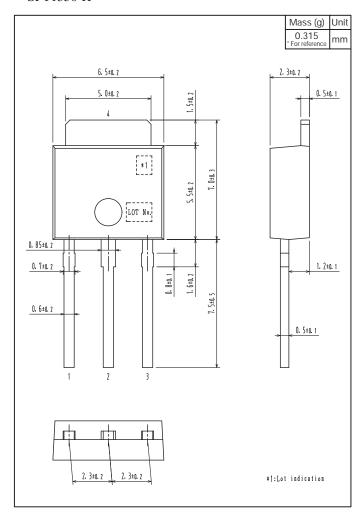


Lab	e l	JEITA Phase		
LEAD F	REE 3	JEITA	Phase	3 A
LEAD F	REE 4	JEITA	Phase	3



Outline Drawing

SFT1350-H



Note on usage: Since the SFT1350 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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